



# Product data sheet

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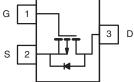




**General Features** 

 $V_{DS}$  =-60V,I  $_{D}$  =-2A R<sub>DS(ON)</sub> <160m $\Omega$  @ V<sub>GS</sub>=-10V R<sub>DS(ON)</sub> <200m $\Omega$  @ V<sub>GS</sub>=-4.5V

# SOT-23



#### Application

Load switch PWM application

#### Absolute Maximum Ratings (TA=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	-60	V
V <sub>G</sub> s	Gate-Source Voltage	±20	V
Ι <sub>D</sub>	Drain Current-Continuous	-2	A
Ідм	Drain Current-Pulsed (Note 1)	-8	А
PD	Maximum Power Dissipation	1.5	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	83.3	°C <b>/W</b>



#### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	BV <sub>DSS</sub> V <sub>GS</sub> =0V I <sub>D</sub> =-250μA		-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub> V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V		-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1.4	-2.0	-2.6	V
Drain Course On Clate Desistance		V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.5A	-	140	160	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	-	160	200	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =-5V,I <sub>D</sub> =-1.5A	-	3	-	S
Dynamic Characteristics (Note4)	·		•			
Input Capacitance	C <sub>lss</sub>		-	444.2	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V, F=1.0MHz	-	19.6	-	PF
Reverse Transfer Capacitance	Crss		-	17.9	-	PF
Switching Characteristics (Note 4)	·		•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	40	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =-30V, I <sub>D</sub> =-1.5A,	-	35	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V,R <sub>G</sub> =3Ω	-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	11.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-30,I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-10V	-	2.7	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	v <sub>GS</sub> =-10V	-	1.6	_	nC
Drain-Source Diode Characteristics			·	·		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-1.5A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-1.6	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ <b>=</b> 25°C, I <sub>F</sub> <b>=</b> - 1.5A	-	25		nS
Reverse Recovery Charge	Qrr	di/dt = -100A/ $\mu$ s <sup>(Note3)</sup>	-	31		nC

#### Notes:

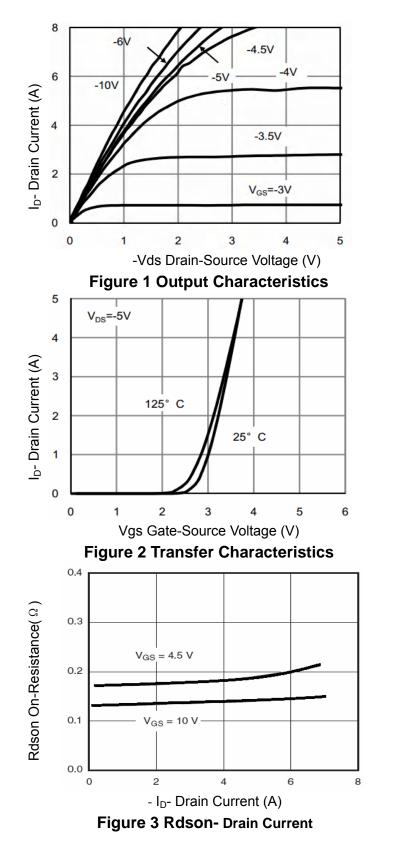
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

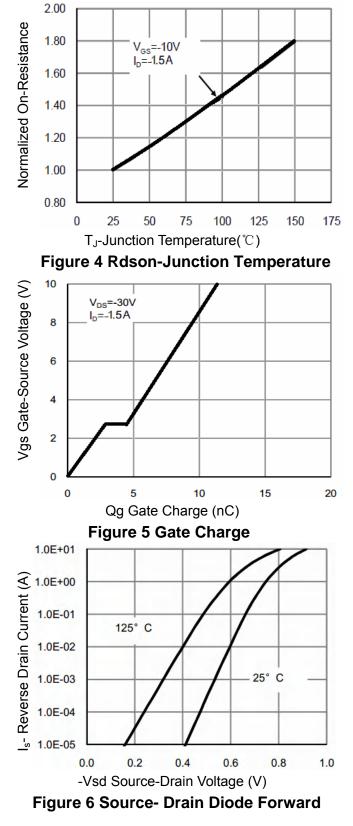
**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



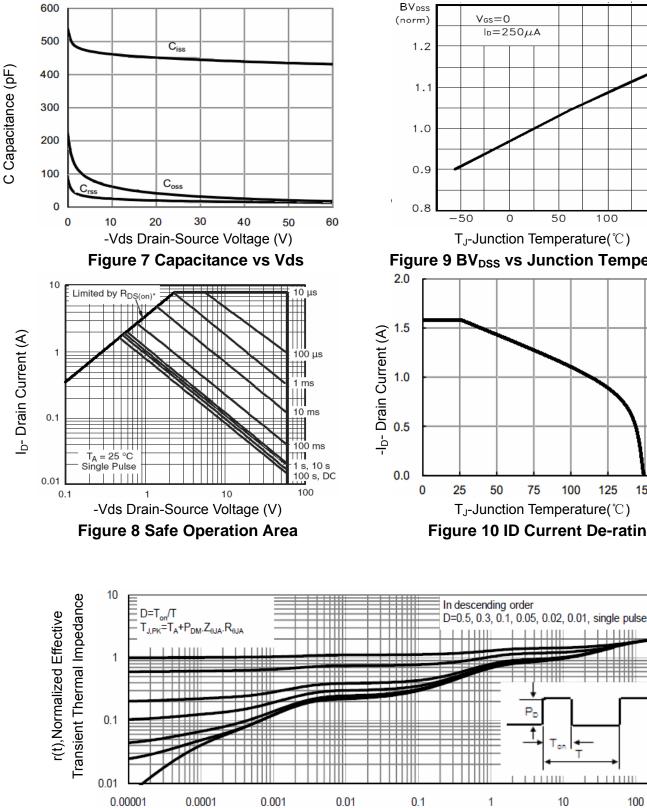


#### **Typical Electrical and Thermal Characteristics (Curves)**





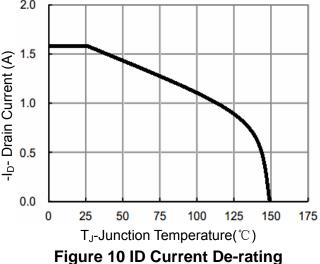
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Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance

50 100 TJ(°C) T<sub>J</sub>-Junction Temperature ( $^{\circ}C$ )

Figure 9 BV<sub>DSS</sub> vs Junction Temperature



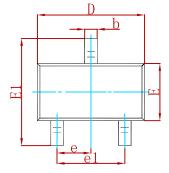
1000

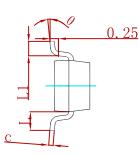
100

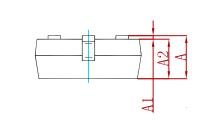


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#### PACKAGE MECHANICAL DATA

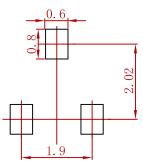






Sump of	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	) TYP	0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550	) REF	0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

#### Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
SI2309CDS-T1-MS	SOT-23	3000



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